

What is claimed is:

1. A method of forming a resist pattern comprising steps of:

5 forming a resin layer, which includes a benzophenone compound, on a substrate surface;
 forming a photoresist layer on a surface of the resin layer;
 forming a latent image by irradiating the
10 photoresist layer with an exposure beam with a wavelength of 100nm to 300nm inclusive; and
 forming a resist pattern with recessed and protruding parts in the photoresist layer by developing the photoresist layer in which the latent image has
15 been formed.

2. A method of forming a resist pattern according to Claim 1, wherein the resin layer is formed with a thickness of 100nm to 200nm inclusive and the
20 photoresist layer is formed with a thickness of 120nm to 200nm inclusive.

3. A method of forming a resist pattern according to Claim 2, wherein the photoresist layer is formed with a
25 thickness of 160nm to 200nm inclusive.

4. A resist pattern forming apparatus, comprising:
 a resin layer forming device that forms a resin layer including a benzophenone compound on a substrate
30 surface;

 a photoresist layer forming device that forms a photoresist layer on a surface of the resin layer;
 an exposure device that forms a latent image by

irradiating the photoresist layer with an exposure beam
with a wavelength of 100nm to 300nm inclusive; and a
developing device that forms a resist pattern with
recessed and protruding parts in the photoresist layer
5 by developing the photoresist layer in which the latent
image has been formed.